

1 Supplementary Information

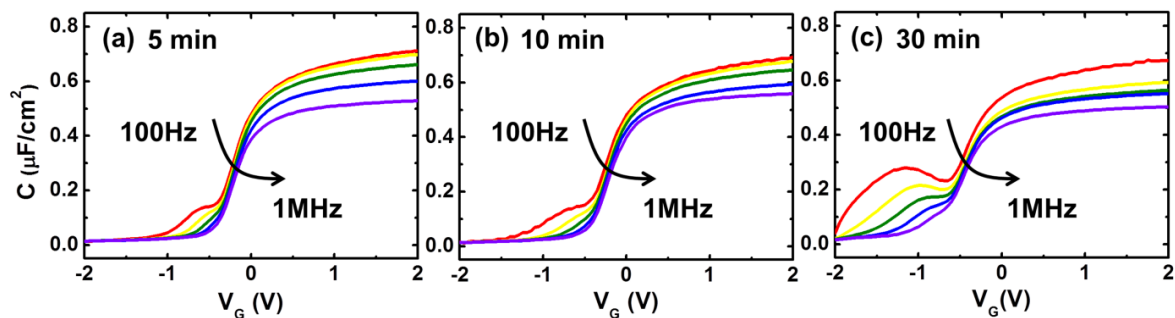
2 **Facile Process for Surface Passivation Using (NH₄)₂S**
 3 **for the InP MOS Capacitor with ALD Al₂O₃**

4 Jung Sub Lee ¹, Tae Young Ahn ^{1,*} and Daewon Kim ^{2,*}

5 ¹ Department of Orthopaedic Surgery and Medical Research Institute, Pusan National University Hospital,
 6 179 Gudeok-ro, Seo-gu, Busan 49241, Korea; jungsublee@pusan.ac.kr

7 ² Department of Electronic Engineering, Institute for Wearable Convergence Electronics, Kyung Hee
 8 University, 1732 Deogyong-daero, Giheung-gu, Yongin 17104, Korea

9 * Correspondence: daewon@khu.ac.kr (D.K.); falconbleu@daum.net (T.Y.A.)



10

11 **Figure S1.** The capacitance-voltage characteristics of the Au/Ni/Al₂O₃/InP which was treated on 10%
 12 (NH₄)₂S for (a) 5, and (b) 10, and (c) 30 min. Measurement frequencies are 100 Hz, 1 kHz, 10 kHz, 100
 13 kHz, and 1 MHz.



© 2019 by the authors. Licensee MDPI, Basel, Switzerland. This article is an open access article distributed under the terms and conditions of the Creative Commons Attribution (CC BY) license (<http://creativecommons.org/licenses/by/4.0/>).